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| ISBN | 1-281-88100-7<br>9786611881009<br>981-256-932-4 |
| Descrizione fisica | 1 online resource (320 p.) |
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| Soggetti | Metal oxide semiconductor field-effect transistors<br>Field-effect transistors<br>Electronic books. |
| Lingua di pubblicazione | Inglese |
| Formato | Materiale a stampa |
| Livello bibliografico | Monografia |
| Note generali | Description based upon print version of record. |
| Nota di bibliografia | Includes bibliographical references and index. |
| Nota di contenuto | Preface; Contents; Chapter 1 Introduction; Chapter 2 RF Power Amplifiers; Chapter 3 MOSFET PHYSICS; Chapter 4 Lateral-Diffused MOSFETs; Chapter 5 Vertical-Diffused MOSFETs; Chapter 6 Charge-Coupled MOSFETs; Chapter 7 Super-Linear MOSFETs; Chapter 8 Planar Super-Linear MOSFETs; Chapter 9 Dual Trench MOSFETs; Chapter 10 Hot Carrier Injection Instability; Chapter 11 Synopsis; Appendix; Index |
| Sommario/riassunto | The world-wide proliferation of cellular networks has revolutionizedtelecommunication systems.  The transition from Analog to Digital RFtechnology enabled substantial increase in voice traffic usingavailable spectrum, and subsequently the delivery of digitally basedtext messaging, graphics and even streaming video. |